

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
728-203 DIVSERIAL NO.
10/666,972APPLICANTS
Louis L. HSU, et al.FILING DATE
September 19, 2003GROUP ART UNIT
not yet knownINFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
hr	5,539,217	07/23/1996	Edmond et al.			
	5,742,076	04/21/1998	Sridevan et al.			
d	5,925,895	07/20/1999	Sriram et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

by		Nemati et al, "A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device", 1 on VLSI Technology Digest of Technical Papers, IEEE, pages 66-67, 1998.
by		Nemati et al, "A Novel Thyristor-based SRAM Cell (T-RAM) for High Speed, Low-Voltage, Gig Memories", IEDM 1999, 283-286

EXAMINER

DATE CONSIDERED

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.